

Vishay Siliconix

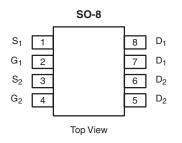
Dual P-Channel 2.5-V (G-S) MOSFET

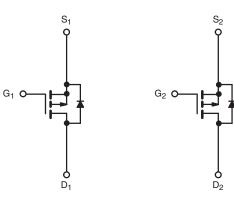
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
- 20	0.032 at V _{GS} = - 4.5 V	- 6.5		
- 20	0.050 at V _{GS} = - 2.5 V	- 5.2		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- Compliant to RoHS Directive 2002/95/EC







Ordering Information: Si4963BDY-T1-E3 (Lead (Pb)-free) Si4963BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
	T _A = 25 °C	– I _D	- 6.5	- 4.9	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 5.2	- 3.9	
Pulsed Drain Current		I _{DM}	- 40		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 1.7	- 0.9	
	T _A = 25 °C	PD	2.0	1.1	w
Maximum Power Dissipation ^a	T _A = 70 °C	r D	1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	- R _{thJA}	58	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		91	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	34	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

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Parameter	Symbol	Test Conditions Min		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.6		- 1.4	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA		
		$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	μΑ		
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 5			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 20			А		
	D	V _{GS} = - 4.5 V, I _D = - 6.5 A		0.025	0.032	0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2 A		0.040	0.050	Ω		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6.5 A		18		S		
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = - 1.7 A, $V_{\rm GS}$ = 0 V		- 0.75	- 1.2	V		
Dynamic ^b				1				
Total Gate Charge	Qg			14	21			
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 6.5 A		2.6		nC		
Gate-Drain Charge	Q _{gd}			4.6				
Gate Resistance	R _g	f = 1 MHz		8.3		Ω		
Turn-On Delay Time	t _{d(on)}			30	45			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		40	60			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		80	120	ns		
Fall Time	t _f			55	85			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		40	80			

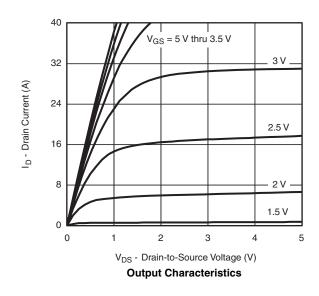
Notes:

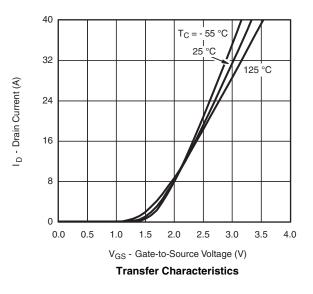
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

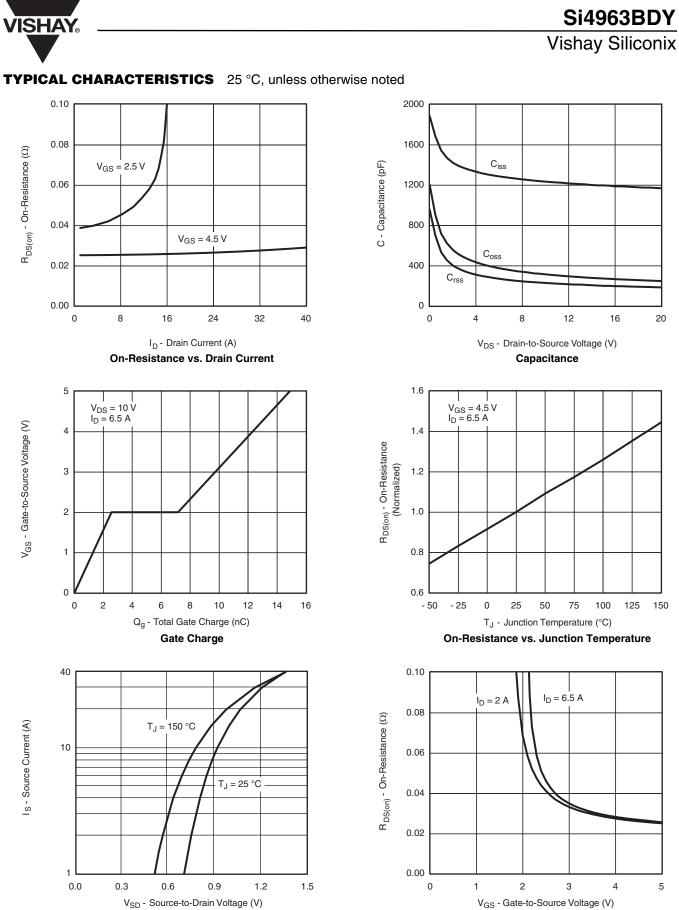
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





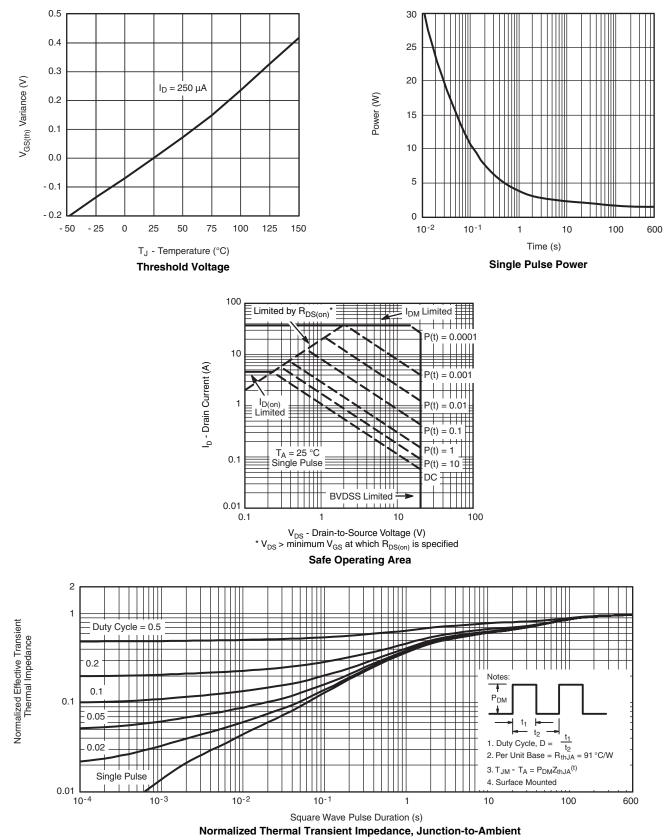


Document Number: 72753 S09-0704-Rev. B, 27-Apr-09 On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



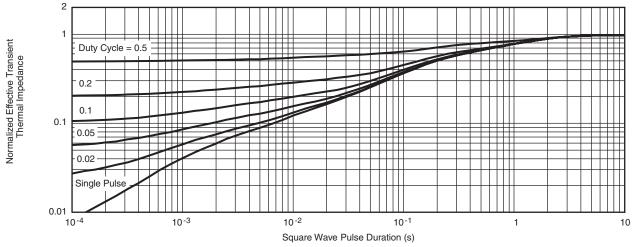




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg772753.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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